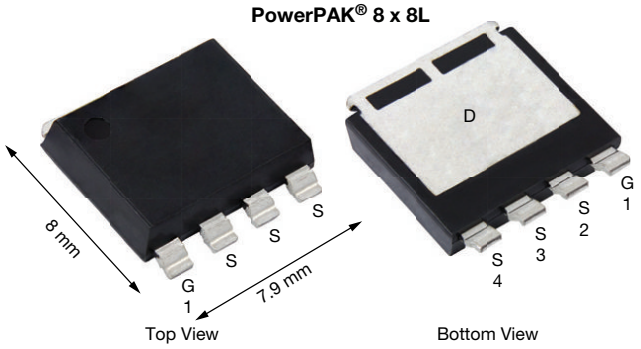
Automotive N-Channel 40 V (D-S) 175 °C MOSFET



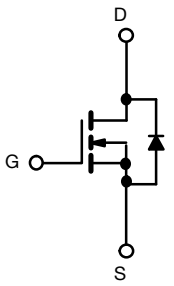
FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.6 mm package
- Very low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

RoHS COMPLIANT

HALOGEN FREE



N-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.00124
I_D (A) [e]	345
Configuration	Single

ORDERING INFORMATION	
Package	PowerPAK 8 x 8L
Lead (Pb)-free and halogen-free	SQJQ142E (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	40	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current [e]	T_C = 25 °C	I_D	345	A
	T_C = 125 °C		199	
Continuous source current (diode conduction) [e]		I_S	252	
Pulsed drain current [a, e]		I_{DM}	791	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	48	
Single pulse avalanche energy		E_{AS}	115.2	mJ
Maximum power dissipation [e]	T_C = 25 °C	P_D	277	W
	T_C = 125 °C		92	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) [c]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount [c]	R_{thJA}	44	°C/W
Junction-to-case (drain) [d]		R_{thJC}	0.54	

Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. When mounted on 1" square PCB (FR4 material)
c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
d. As per JESD51-14
e. Values based on R_{thJC} and T_C of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system

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SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0, I_D = 250 µA		40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2	3	3.5	
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 40 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 125 °C	-	-	200	
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 175 °C	-	-	330	
On-state drain current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	100	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 20 A	-	0.00100	0.00124	Ω
		V_{GS} = 10 V	I_D = 20 A, T_J = 125 °C	-	-	0.00200	
		V_{GS} = 10 V	I_D = 20 A, T_J = 175 °C	-	-	0.00240	
Forward transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 60 A		-	150	-	S
Dynamic [b]							
Input capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	5360	6975	pF
Output capacitance	C_{oss}			-	2070	2700	
Reverse transfer capacitance	C_{rss}			-	167	215	
Total gate charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 20 A	-	92	130	nC
Gate-source charge [c]	Q_{gs}			-	26	-	
Gate-drain charge [c]	Q_{gd}			-	20.1	-	
Gate resistance	R_g	f = 1 MHz		0.65	1.59	2.56	Ω
Turn-on delay time [c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 1 Ω I_D ≅ 20 A, V_{GEN} = 10 V, R_g = 1 Ω		-	18.5	26	ns
Rise time [c]	t_r			-	18	25	
Turn-off delay time [c]	$t_{d(off)}$			-	37	52	
Fall time [c]	t_f			-	14	20	
Source-Drain Diode Ratings and Characteristics [b]							
Reverse recovery time	t_{rr}	V_{DD} = 32 V, I_{FM} = 15 A, di/dt = 100 A/µs		-	59	-	ns
Reverse recovery charge	Q_{rr}			-	69	-	nC
Reverse recovery current	I_{RM}			-	2	3.2	A
Pulsed current [a]	I_{SM}			-	-	719	A
Forward voltage	V_{SD}	I_F = 50 A, V_{GS} = 0		-	0.8	1.1	V

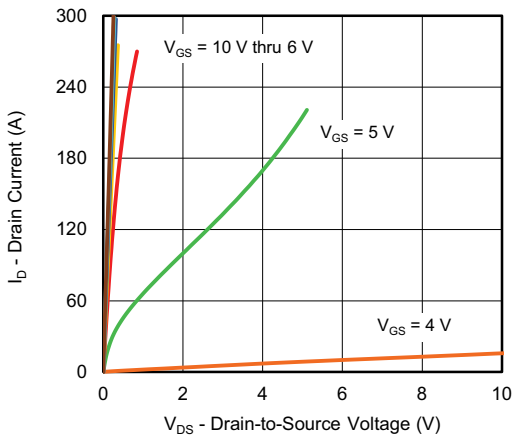
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

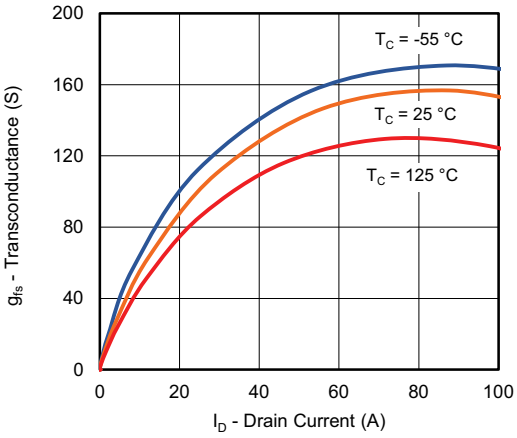
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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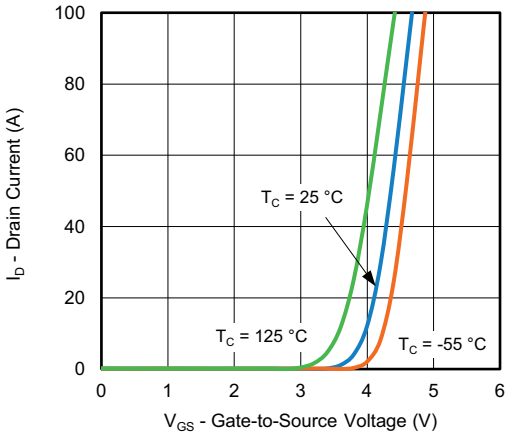
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



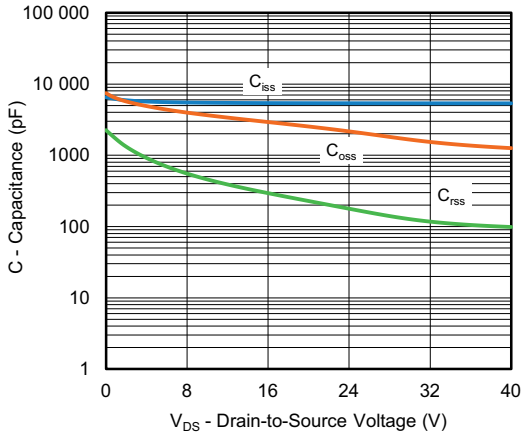
Output Characteristics



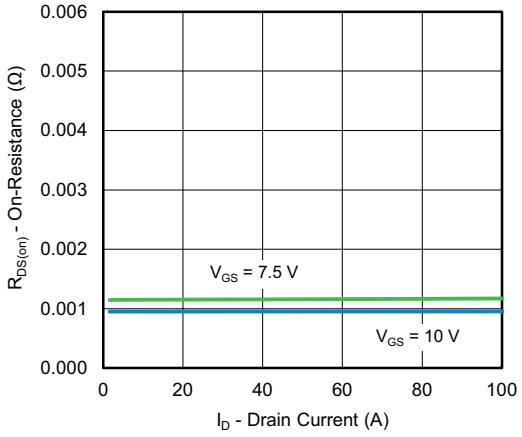
Transconductance



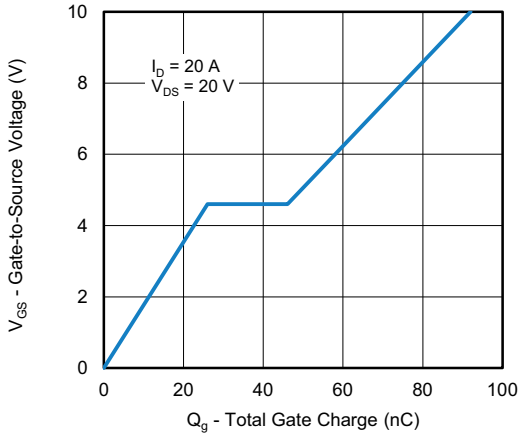
Transfer Characteristics



Capacitance



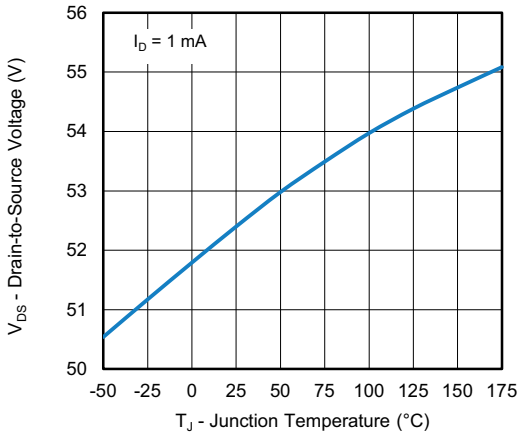
On-Resistance vs. Drain Current



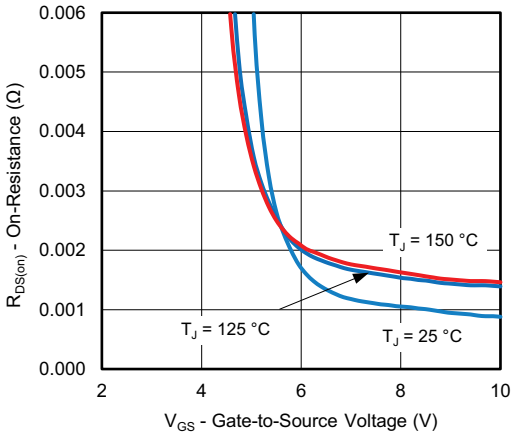
Gate Charge

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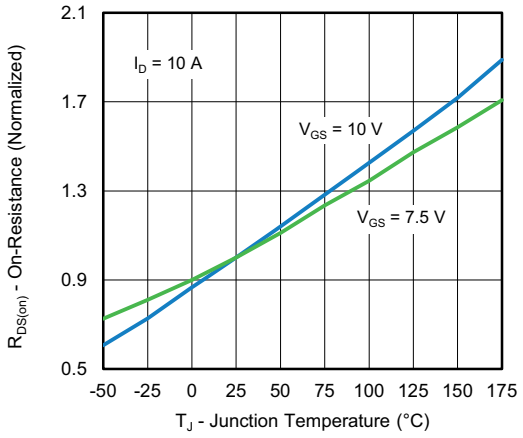
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



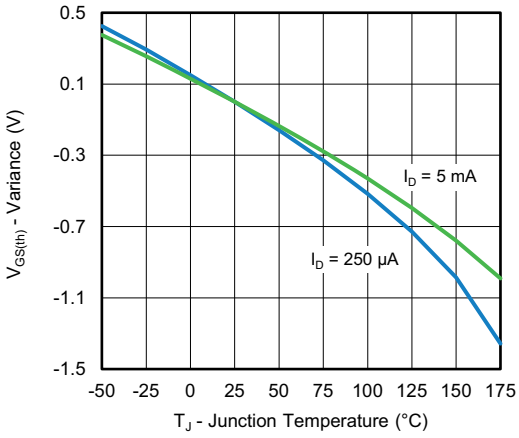
Drain Source Breakdown vs. Junction Temperature



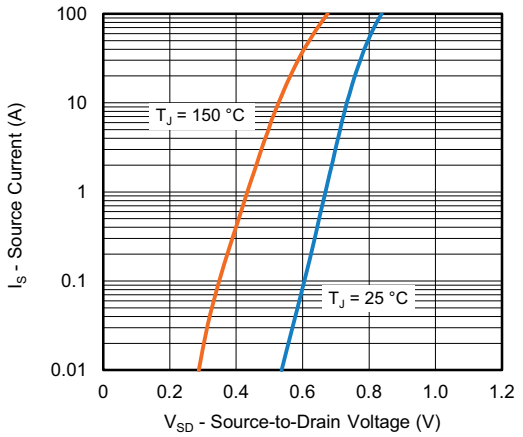
On-Resistance vs. Gate-to-Source Voltage



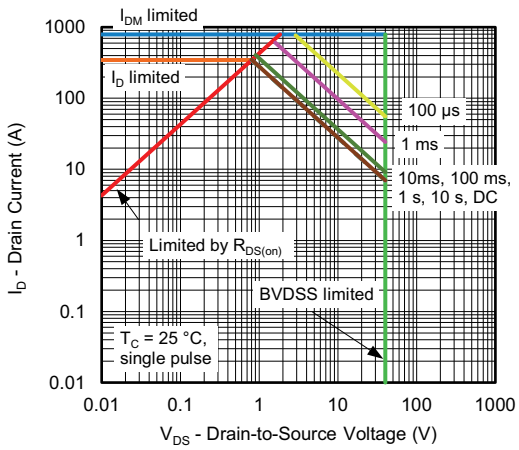
On-Resistance vs. Junction Temperature



Threshold Voltage



Source Drain Diode Forward Voltage



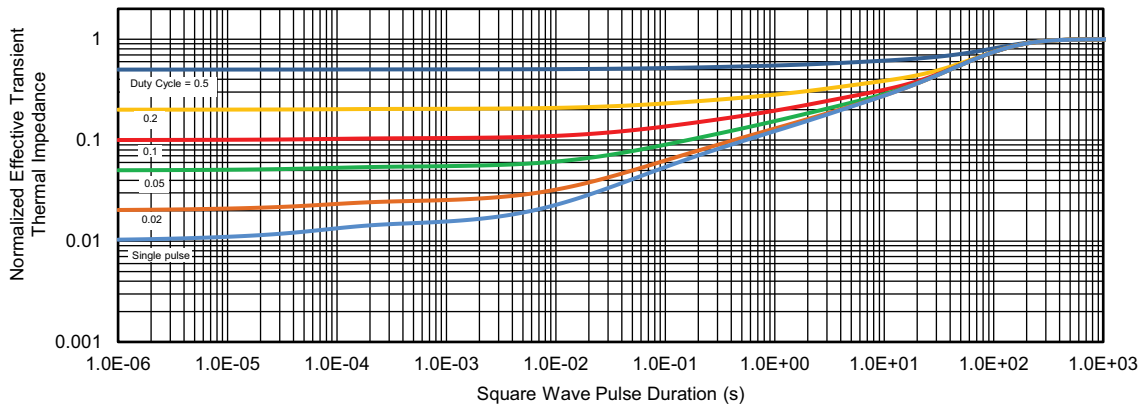
Safe Operating Area

Note

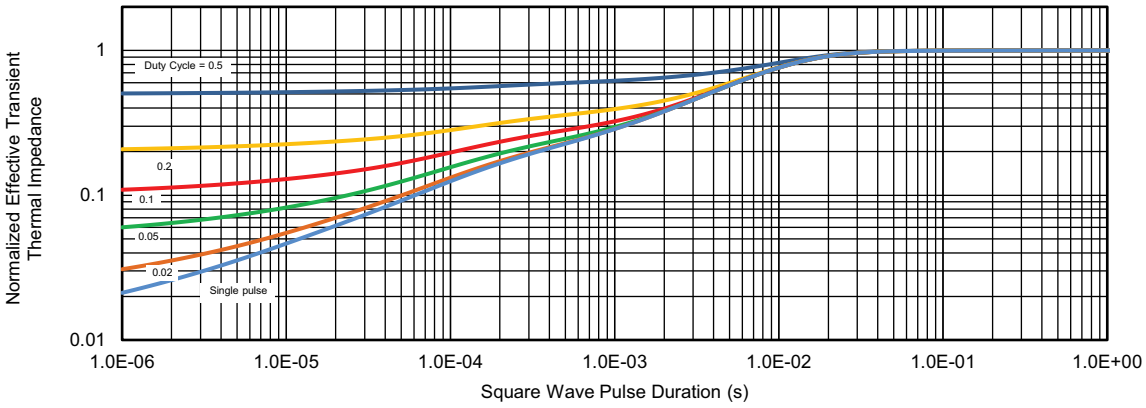
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

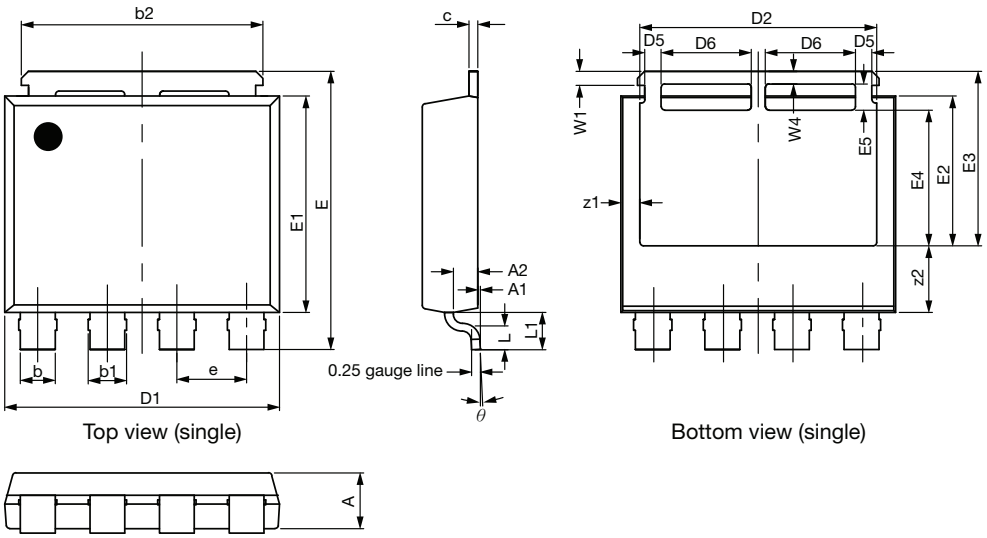


Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK® 8 x 8L BWL Case Outline 2



Top view (single)

Bottom view (single)

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.50	1.60	1.70	0.059	0.063	0.067
A1	0.00	-	0.127	0.000	-	0.005
A2	0.655	0.705	0.755	0.026	0.028	0.030
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	6.84	6.94	7.04	0.269	0.273	0.277
c	0.20	0.25	0.30	0.008	0.010	0.012
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
e	1.97	2.00	2.03	0.078	0.079	0.080
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	4.21	4.31	4.41	0.166	0.170	0.174
E3	4.92	5.02	5.12	0.194	0.198	0.202
E4	3.80	3.90	4.00	0.150	0.154	0.157
E5	0.65	0.75	0.85	0.026	0.030	0.033
L	0.61	0.68	0.75	0.024	0.027	0.030
L1	1.00	1.07	1.15	0.039	0.042	0.045
W1	0.30	0.40	0.50	0.012	0.016	0.020
W4	0.32	0.37	0.42	0.013	0.015	0.017
z1	0.45	0.55	0.65	0.018	0.022	0.026
z2	1.81	1.91	2.01	0.071	0.075	0.079
θ	0°	-	5°	0°	-	5°
ECN: S19-0643-Rev. B, 05-Aug-2019 DWG: 6073						

Note

- Millimeter will govern

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